# Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

# **High-Performance Silicon-Gate CMOS**

The MC74HC244A is identical in pinout to the LS244. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This octal noninverting buffer/line driver/line receiver is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has noninverting outputs and two active-low output enables.

The HC244A is similar in function to the HC240A.

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 136 FETs or 34 Equivalent Gates
- Pb-Free Packages are Available\*



## ON Semiconductor®

http://onsemi.com

## MARKING DIAGRAMS

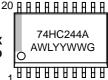


PDIP-20 N SUFFIX CASE 738

20 AAAAAAAAAAA MC74HC244AN O AWLYYWWG

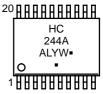


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 F SUFFIX CASE 967

A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package
= Pb-Free Package

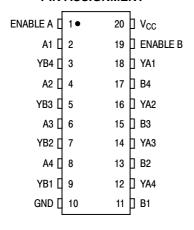
(Note: Microdot may be in either location)

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

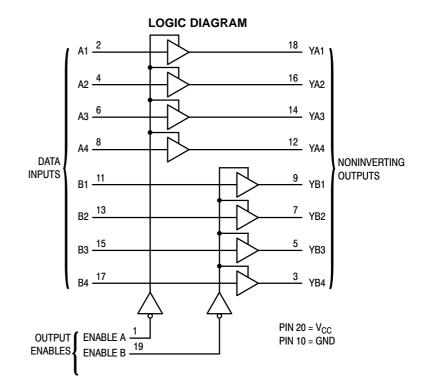
## **PIN ASSIGNMENT**



## **FUNCTION TABLE**

Inpu	Inputs				
Enable A, Enable B	A, B	YA, YB			
L	L	L			
L	Н	Н			
Н	Х	Z			

Z = high impedance



## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC244AN	PDIP-20	18 Units / Rail
MC74HC244ANG	PDIP-20 (Pb-Free)	18 Units / Rail
MC74HC244ADW	SOIC-20 WIDE	38 Units / Rail
MC74HC244ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC244ADWR2	SOIC-20 WIDE	1000 Tape & Reel
MC74HC244ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC244ADT	TSSOP-20*	75 Units / Rail
MC74HC244ADTG	TSSOP-20*	75 Units / Rail
MC74HC244ADTR2	TSSOP-20*	2500 Tape & Reel
MC74HC244ADTR2G	TSSOP-20*	2500 Tape & Reel
MC74HC244AF	SOEIAJ-20	40 Units / Rail
MC74HC244AFG	SOEIAJ-20 (Pb-Free)	40 Units / Rail
MC74HC244AFEL	SOEIAJ-20	2000 Tape & Reel
MC74HC244AFELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 35	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)			6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)			V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types			+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 2$ (Figure 1) $V_{CC} = 4$ $V_{CC} = 6$	.5 V	0 0 0	1000 500 400	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V <sub>OH</sub>	Minimum High–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned}  V_{in} = V_{IH} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IL} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

NOTE: Information on typical parametric values and high frequency or heavy load considerations can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_f = t_f = 6 \text{ ns}$ )

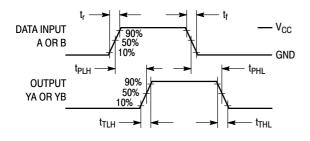
			Gu	Guaranteed Limit		
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤85°C	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	2.0 3.0 4.5 6.0	96 50 18 15	115 60 23 20	135 70 27 23	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 32 18 15	ns
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High–Impedance State)	_	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	34	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

### **SWITCHING WAVEFORMS**



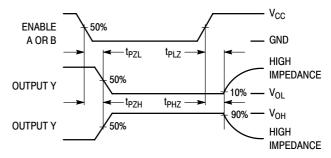
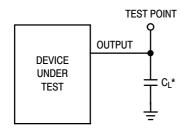


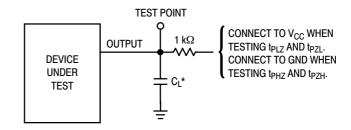
Figure 1.

Figure 2.

## **TEST CIRCUITS**



\*Includes all probe and jig capacitance



\*Includes all probe and jig capacitance

Figure 3. Test Circuit

Figure 4. Test Circuit

## **PIN DESCRIPTIONS**

## **INPUTS**

A1, A2, A3, A4, B1, B2, B3, B4 (Pins 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in noninverted form on the corresponding Y outputs, when the outputs are enabled.

## **CONTROLS**

## Enable A, Enable B (Pins 1, 19)

Output enables (active-low). When a low level is applied to these pins, the outputs are enabled and the devices

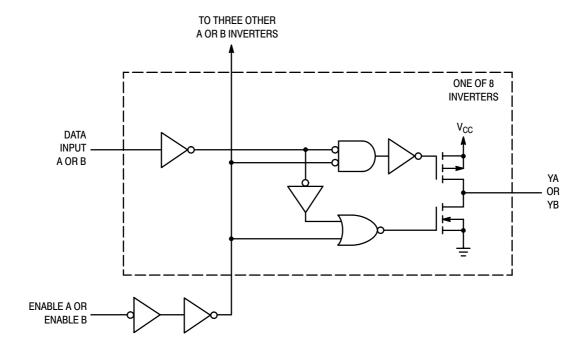
function as noninverting buffers. When a high level is applied, the outputs assume the high impedance state.

## **OUTPUTS**

YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4 (Pins 18, 16, 14, 12, 9, 7, 5, 3)

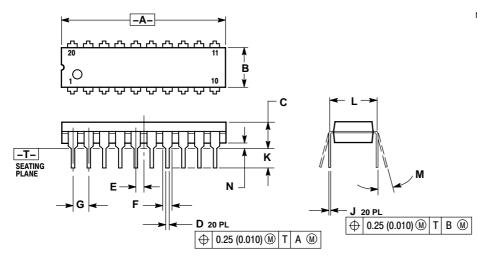
Device outputs. Depending upon the state of the output–enable pins, these outputs are either noninverting outputs or high–impedance outputs.

## **LOGIC DETAIL**



#### PACKAGE DIMENSIONS

## PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 **ISSUE E**



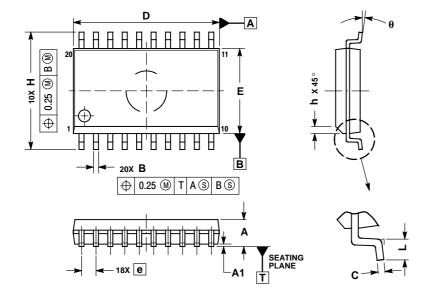
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI

- 1. DIMENSIONING AND TOLEHANCING PER AI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
E	0.050 BSC		1.27	BSC	
F	0.050	0.070	1.27	1.77	
G	0.100 BSC		2.54	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300	BSC	7.62 BSC		
М	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

## SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**

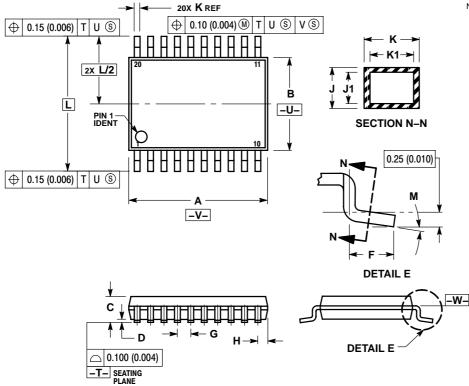


- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
Е	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

#### **PACKAGE DIMENSIONS**

## TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



#### NOTES:

- DTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SILLIAL NOT EXCEPT A 45 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER
- SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

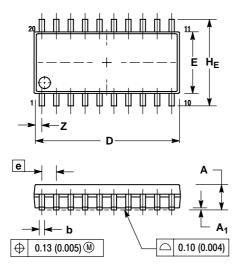
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

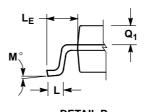
  6. TERMINAL NUMBERS ARE SHOWN.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

_				
	MILLIMETERS INCH			HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	0.65 BSC		BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	6.40 BSC		BSC
M	0°	8°	0°	8°

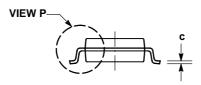
## **PACKAGE DIMENSIONS**

## SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE O**





**DETAIL P** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI

- NOTES:

  1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2 CONTROLLING DIMENSION: MILLIMETER.

  3 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A <sub>1</sub>	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.18	0.27	0.007	0.011	
D	12.35	12.80	0.486	0.504	
E	5.10	5.45	0.201	0.215	
е	1.27 BSC		0.050	BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10 °	0 °	10 °	
$Q_1$	0.70	0.90	0.028	0.035	
Z		0.81		0.032	

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.